

P-channel Enhancement Mode Power MOSFET

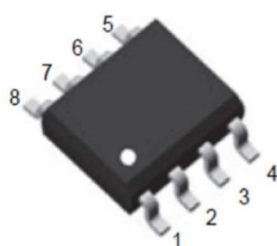
Features

- $V_{DS} = -60V$, $I_D = -7A$
 $R_{DS(ON)} < 55m\Omega$ @ $V_{GS} = -10V$
 $R_{DS(ON)} < 65m\Omega$ @ $V_{GS} = -4.5V$

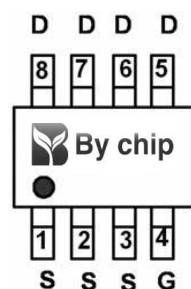
General Features

- Advanced Trench Technology
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free and Green Available

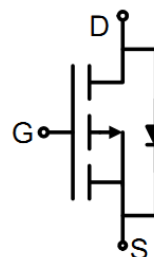
100% UIS TESTED!
100% ΔV_{ds} TESTED!



SOP-8



pin assignment



Schematic diagram

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-7	A
Pulsed Drain Current	I_{DM}	-30	A
Maximum Power Dissipation	P_D	3.0	W
Single pulse avalanche energy ^(Note 5)	E_{AS}	65	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JC}$	41.7	$^\circ C/W$
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Electrical Characteristics (T_C=25°C unless otherwise noted)

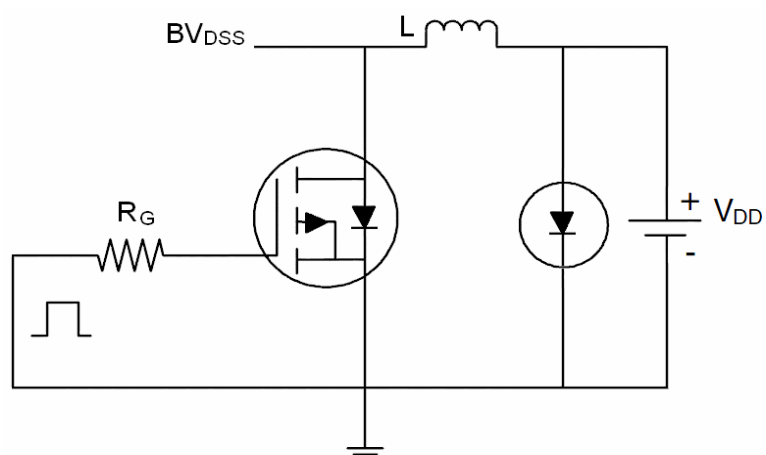
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.0		-3.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-7A	-		55	mΩ
		V _{GS} =-4.5V, I _D =-7A	-		65	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-7A	-	15	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{iss}	V _{DS} =-30V, V _{GS} =0V, F=1.0MHz	-	1108	-	PF
Output Capacitance	C _{oss}		-	73.7	-	PF
Reverse Transfer Capacitance	C _{rss}		-	58.2	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-30V, R _L =4.2Ω, V _{GS} =-10V, R _G =3Ω	-	8	-	nS
Turn-on Rise Time	t _r		-	4	-	nS
Turn-Off Delay Time	t _{d(off)}		-	32	-	nS
Turn-Off Fall Time	t _f		-	7	-	nS
Total Gate Charge	Q _g	V _{DS} =-30, I _D =-7A, V _{GS} =-10V	-	23.4	-	nC
Gate-Source Charge	Q _{gs}		-	4.1	-	nC
Gate-Drain Charge	Q _{gd}		-	4.8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =-7A	-		-1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	-7	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =- 7A	-	25		nS
Reverse Recovery Charge	Q _{rr}	di/dt = -100A/μs ^(Note3)	-	31		nC

Notes:

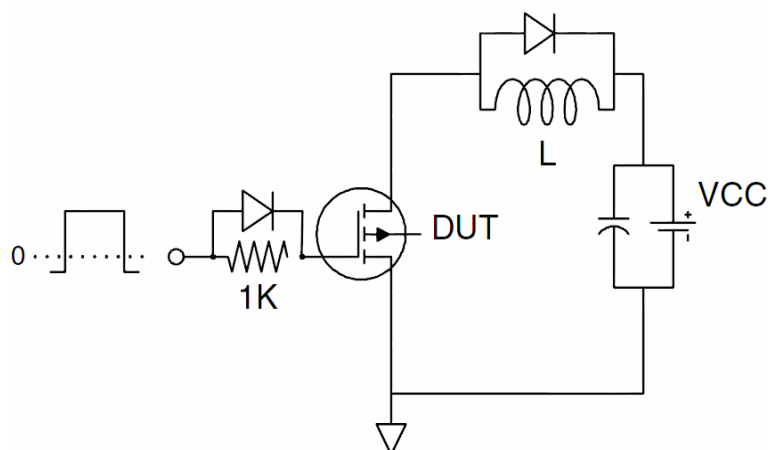
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Test Circuit

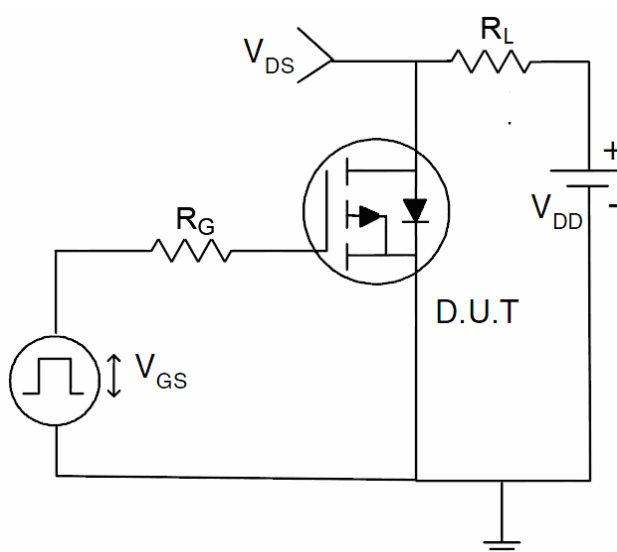
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

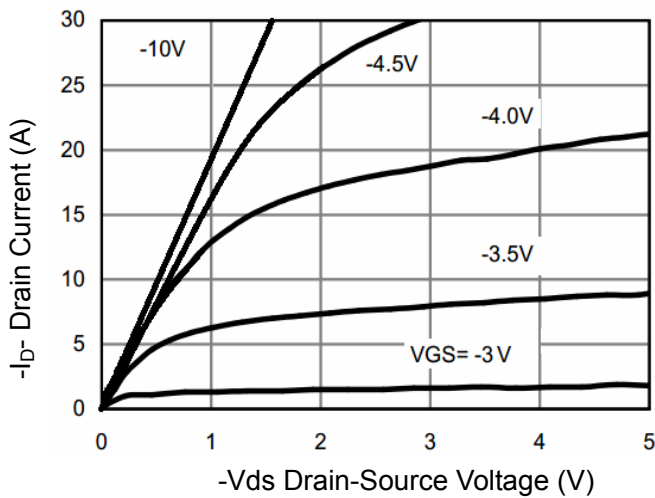


Figure 1 Output Characteristics

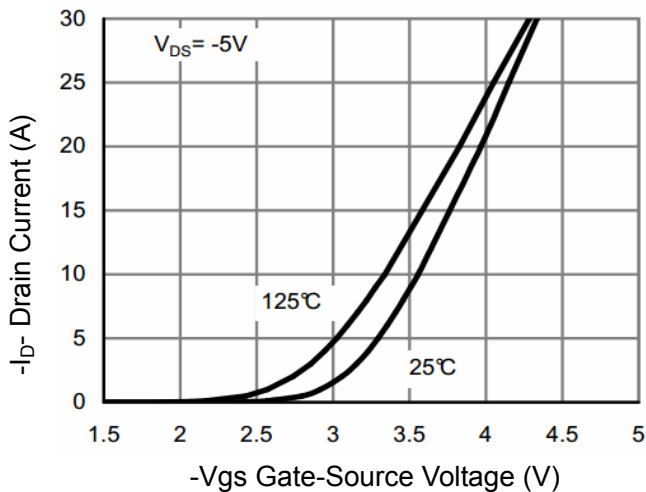


Figure 2 Transfer Characteristics

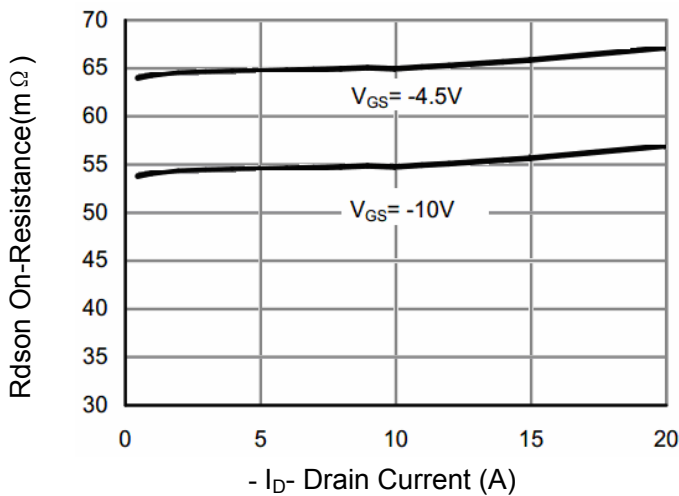


Figure 3 Rdson- Drain Current

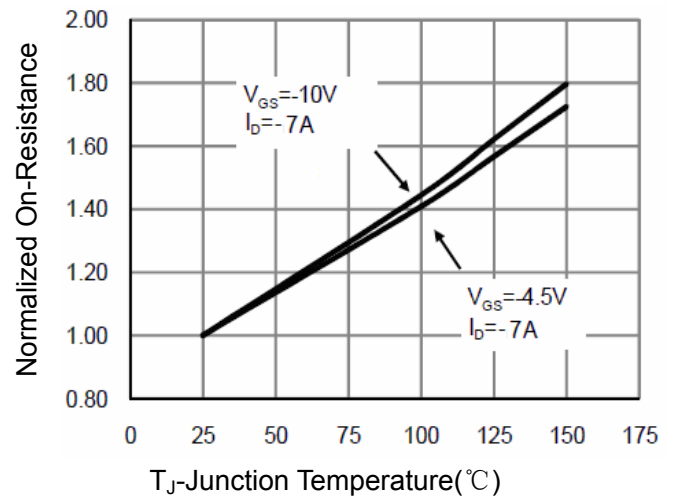


Figure 4 Rdson-Junction Temperature

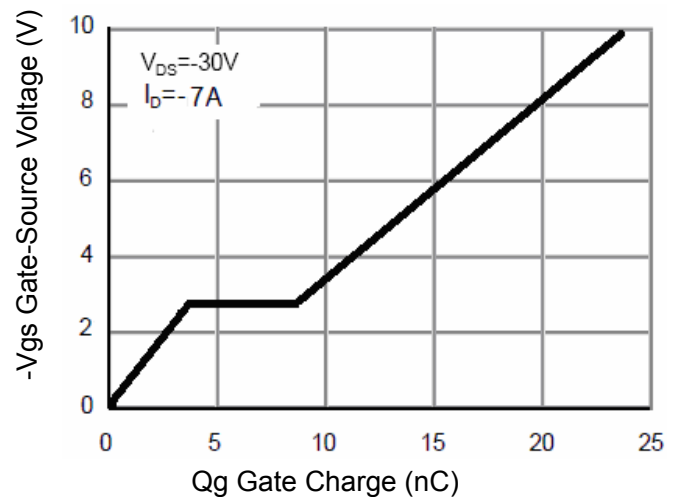


Figure 5 Gate Charge

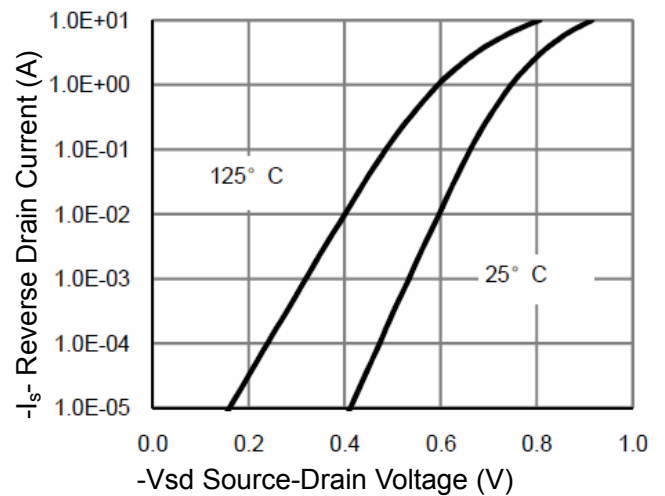


Figure 6 Source- Drain Diode Forward

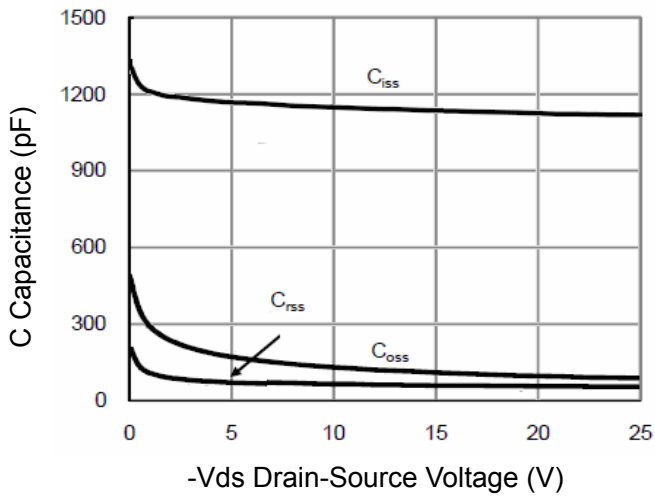


Figure 7 Capacitance vs Vds

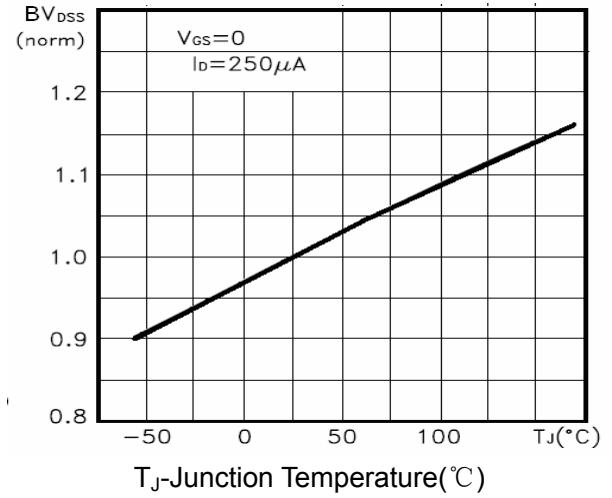


Figure 9 BV_{DSS} vs Junction Temperature

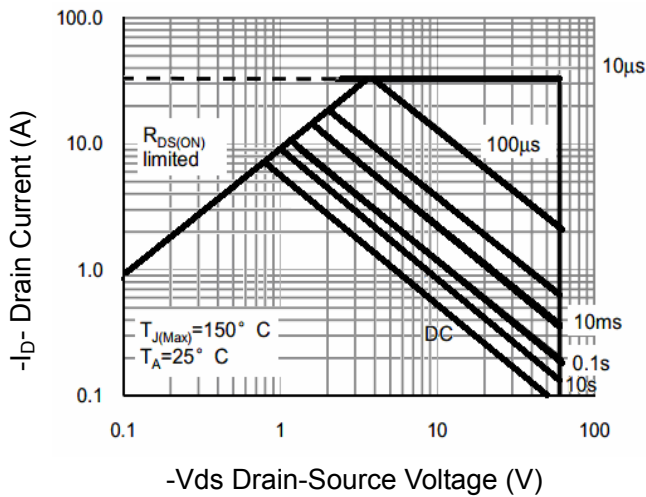


Figure 8 Safe Operation Area

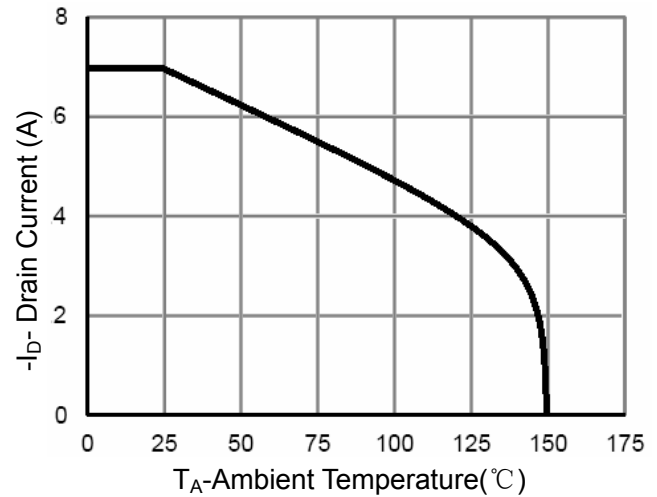


Figure 10 I_D Current De-rating

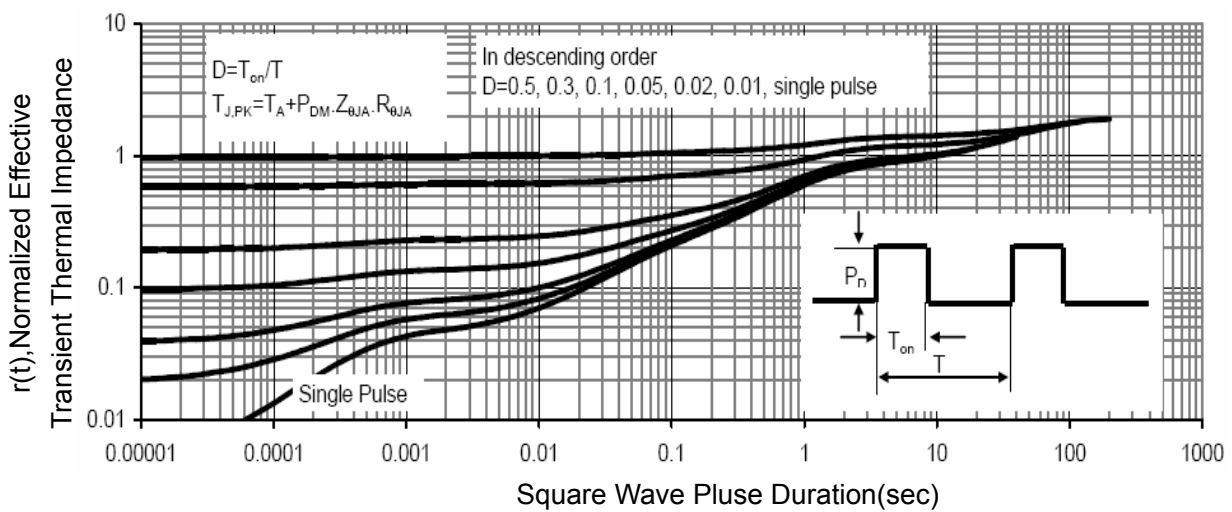


Figure 11 Normalized Maximum Transient Thermal Impedance